

3DK100, 3DK101**NPN Silicon High Frequency Low Power Switch Transistor****Features:**

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation and high frequency switch, high frequency small signal amplification, low power source adjustment circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications					
			3DK100			3DK101		
			A	B	C	A	B	C
Total Dissipation	P_{tot}	mW	100 (Ta=25°C)			200 (Ta=25°C)		
Max. Collector Current	I_{CM}	mA	30			40		
Junction Temperature	T_{jm}	°C	175					
Storage Temperature	T_{stg}	°C	-55~+175					
C-B Breakdown Voltage	$V_{(BR)CBO}$	V	20	20	15	30	30	20
			Ic=0.1mA					
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	15	15	10	20	25	15
			Ic=0.1mA					
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	≥4 (IE=0.1 mA)					
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.3 (Ic=10mA, IB=1mA)			0.3 (Ic=20mA, IB=2mA)		
Base- Emitter Saturation Voltage Drop	$V_{BE(sat)}$	V	0.9 (Ic=10mA, IB=1mA)			0.9 (Ic=20mA, IB=2mA)		
C-E Leakage Current	I_{CEO}	uA	0.1 (VCE=6V)			0.1 (VCE=10V)		
DC Current Gain	h_{FE}		Orange:25~40, Yellow:40~55, Green:55~80, Blue:80~120, Purple:120~180					
			(VCE=1V, Ic=10mA)			(VCE=1V, Ic=20mA)		
Transition frequency	f_T	MHz	300 (VCE=6V, Ic=3mA, f=100MHz)			300 (VCE=10V, Ic=10mA, f=100MHz)		
Turn-on Time	Ic=10 mA IB1= IB2=1mA	ton	20			30		
Storage Time		ts	20	10		40	20	15
Fall Time		tf	15			20		

Outline and Dimensions: